

MPFF600R12MBF 1200V600A IGBT Module

Electrical Features

- Trench/Fieldstop IGBT
- Low VCE(sat)
- VCE(sat) with positive temperature coefficient
- $10 \ \mu \ s$ short circuit capability
- Fast&soft reverse recovery anti-parallel FWD
- Low inductance case



Typical Applications

- Motor Drives
- High Power Converters
- UPS System
- Servo Drives
- Wind Turbines

IGBT, Inverter

Maximu	m Rated Values						
Symbol	Item	Conditions		Rating		Unit	
IGBT							
V _{CES}	Collector-emitter voltage	T _{vj} =25°C	T _{vj} =25°C			1200	
V _{GES}	Gate-emitter voltage	-			±20		V
Ic	Collector current,DC	T _C =100°C,T _{vj} =175°	T _c =100°C,T _{vj} =175°C			600	
I _{CRM}	Repetitive peak collector current	t _p =1ms			12	00	Α
t _{SC}	Short circuit withstand time	V _{GE} =15V, V _{CC} =600	$V_{GE}=15V, V_{CC}=600V, T_{vj}\leq 150^{\circ}C$			0	μs
P _{tot}	Total power dissipation	T _C =25°C,T _{vj} =175°C	$T_{c}=25^{\circ}C, T_{vj}=175^{\circ}C$			38	W
Charact	eristics Values	·					
Symbol	Item	Conditions			Values		Unit
IGBT	·	·		Min.	Тур.	Max.	
ICES	Collector-emitter cut-off current	V _{CE} =1200V,V _{GE} =0V,T _{vj} =25°C		-	-	3	mA
I _{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$		-	-	400	nA
V _{GE(th)}	Gate-emitter threshold voltage	$I_C=23mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$		5.0	5.7	7.0	
	Collector-emitter saturation voltage	$I_{c}=600A$	T _{vj} =25°C	-	2.2	2.4	
V _{CEsat}			T _{vj} =125°C	-	2.7	-	V
		$V_{GE}=15V$	T _{vj} =150°C	-	2.9	-	
Cies	Input capacitance	- V _{CE} =25V,V _{GE} =0V f=1MHz,T _{vj} =25°C		-	49.77	-	
Coes	Output capacitance			-	2.28	-	nF
Cres	Reverse transfer capacitance			-	2.22	-]
Q _G	Gate charge	$V_{GE}=\pm 15V$		-	7.5	-	nC
Rg	Internal gate resistance	T _{vj} =25°C		-	0.28	-	Ω

			$T_{vj}=25^{\circ}C$	-	272	-	
t _{d(on)}	Turn-on delay time		T _{vj} =125°C	-	253	-	-
		_	T _{vj} =150°C	-	249	-	
			T _{vj} =25°C	-	264	-	
t _r	Rise time		T _{vj} =125°C	-	262	-	-
	_	T _{vj} =150°C	-	259	-	ns	
		V _{CC} =600V,	T _{vj} =25°C	-	1019	-	-
$t_{d(\mathrm{off})}$	Turn-off delay time	Ic=600A,	T _{vj} =125°C	-	1096	-	_
		$V_{GE}=\pm 15V$,	T _{vj} =150°C	-	1112	-	_
		$R_{G(on)}=5.1 \Omega$,	T _{vj} =25°C	-	144	-	-
t_{f}	Fall time	$R_{G(off)}=5.1 \Omega$,	T _{vj} =125°C	-	195	-	_
		L _{load} =200uH	T _{vj} =150°C	-	225	-	
			T _{vj} =25°C	-	148.5	-	
Eon	Turn-on energy (per pulse)		T _{vj} =125°C	-	159.4	-	
			T _{vj} =150°C	-	166.9	-	
			T _{vj} =25°C	-	83.9	-	mJ
$E_{\rm off}$	Turn-off energy (per pulse)		T _{vj} =125°C	-	95.6	-	-
			T _{vj} =150°C	-	99.3	-	
R _{thJC}	Thermal resistance, junction to case	per IGBT		-	-	0.031	K/W
			$se=1W/(m \cdot K)$	_	0.035	-	K/W
R _{thCH}	Thermalresistance, case to heatsink	per IGBT/ λgreas					
R _{thCH}	Temperature under switching	per IGB1/ Agreas		-40		150	°C
T_{vjop}	Temperature under switching conditions	per IGB1/ Agreas		-40		150	°C
T _{vjop} Diode, 1	Temperature under switching conditions	per IGB1/ Agreas		-40		150	°C
T _{vjop} Diode, I Maximu	Temperature under switching conditions Inverter m Rated Values			-40			
T _{vjop} Diode, l Maximu Symbol	Temperature under switching conditions Inverter m Rated Values Item		Conditions	-40	Rat	ting	Unit
T _{vjop} Diode, I Maximu Symbol V _{RRM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage	T _{vj} =25°C	Conditions	-40	Rat 12	ting 00	Unit V
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC	C T _{vj} =25°C T _c =100°C,T _{vj} =1:	Conditions	-40	Rat 12 60	ing 00 00	Unit V A
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM}	Temperature under switching conditions Inverter Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current	T _{vj} =25°C	Conditions	-40	Rat 12 60	ting 00	Unit V
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC	C T _{vj} =25°C T _c =100°C,T _{vj} =1:	Conditions 50°C		Rat 12 60	ting 00 00 00	Unit V A
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values	C T _{vj} =25°C T _c =100°C,T _{vj} =1:	Conditions 50°C T _{vj} =25°C		Rat 12 60 12 2.28	ing 00 00	Unit V A A
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM}	Temperature under switching conditions Inverter Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current	$\begin{array}{c c} & & \\ \hline & & \\ T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=13 \\ \hline t_{p}=1ms \end{array}$	Conditions 50°C T _{vj} =25°C T _{vj} =125°C	- -	Rat 12 60 12 2.28 2.51	ting 00 00 00	Unit V A
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values	$ \begin{array}{c c} \hline & & \\ \hline \\ & & \\ \hline \\ \hline$	Conditions $50^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	- -	Rat 12 60 12 2.28 2.51 2.53	ting 00 00 00 - - - -	Unit V A A
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F	Temperature under switching conditions Inverter Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage	$ \begin{array}{c c} \hline & & \\ \hline \\ & & \\ \hline \\ \hline$	Conditions $50^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$	- - -	Rat 12 60 12 2.28 2.51 2.53 159.5	ting 00 00 00 - - - - -	Unit V A A V
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values	$ \begin{array}{c c} \hline & & \\ \hline \\ & & \\ \hline \\ \hline$	Conditions $\overline{T_{vj}=25^{\circ}C}$ $\overline{T_{vj}=125^{\circ}C}$ $\overline{T_{vj}=150^{\circ}C}$ $\overline{T_{vj}=125^{\circ}C}$ $\overline{T_{vj}=125^{\circ}C}$ $\overline{T_{vj}=125^{\circ}C}$	- -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4	ting 00 00 00 - - - -	Unit V A A
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F	Temperature under switching conditions Inverter Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage	$ \begin{array}{c c} \hline & & \\ \hline \\ & & \\ \hline \\ \hline$	Conditions $50^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$	- - - - -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4 249.4	ting 00 00 00 - - - - -	Unit V A A V
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current	$ \begin{array}{c c} \hline & & \\ \hline \\ & & \\ \hline \\ \hline$	Conditions $50^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=25^{\circ}C$	- - - -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4 249.4 516.1	ting 00 00 00 - - - - -	Unit V A A V
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F	Temperature under switching conditions Inverter Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage	$\begin{array}{c c} & & & \\ & & & \\ \hline & & & \\ T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=12 \\ \hline t_{p}=1ms \\ \hline \\ I_{F}=600A \\ V_{GE}=0V \\ \hline \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ $	Conditions $50^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$	- - - - -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4 249.4 516.1 475.9	ting 00 00 	Unit V A A V
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T _{vjop} Diode, I Maximu Symbol V _{RRM} IF IFRM Characte V _F	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current	$ \begin{array}{c c} $	$\begin{array}{c} \hline \\ \hline \\ \hline \\ \hline \\ 50^{\circ}C \\ \hline \\ $	- - - - - - -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4 249.4 516.1 475.9 474.5	ting 00 00 	Unit V A A V A
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F I _{RM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current Reverse recovery time	$\begin{array}{c c} & & & \\ & & & \\ \hline & & & \\ T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=12 \\ \hline t_{p}=1ms \\ \hline \\ I_{F}=600A \\ \hline \\ V_{GE}=0V \\ \hline \\ \hline \\ V_{R}=600V \\ \hline \\ I_{F}=600A \end{array}$	Conditions $50^{\circ}C$ $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=150^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=125^{\circ}C$	- - - - - - - - - - -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4 249.4 516.1 475.9 474.5 35.1	ting 00 00 00 - - - - - - - - - - - - - - -	Unit V A A V A ns
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F I _{RM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current Reverse recovery time	$\begin{array}{c c} & & & \\ & & & \\ \hline & & & \\ T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=12 \\ \hline t_{p}=1ms \\ \hline \\ I_{F}=600A \\ \hline \\ V_{GE}=0V \\ \hline \\ \hline \\ V_{R}=600V \\ \hline \\ I_{F}=600A \end{array}$	$\begin{array}{c} \hline \\ \hline \\ \hline \\ \hline \\ 50^{\circ}C \\ \hline \\ $	- - - - - - - - -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4 249.4 516.1 475.9 474.5 35.1 55.8	ting 00 00 00 - - - - - - - - - - - - - - -	Unit V A A V A ns
T _{vjop} Diode, I Maximu Symbol V _{RRM} I _F I _{FRM} Characte V _F I _{RM}	Temperature under switching conditions Inverter m Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current eristic Values Continuous forward voltage Peak reverse recovery current Reverse recovery time	$\begin{array}{c c} & & & \\ & & & \\ \hline & & & \\ T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=12 \\ \hline t_{p}=1ms \\ \hline \\ I_{F}=600A \\ \hline \\ V_{GE}=0V \\ \hline \\ \hline \\ V_{R}=600V \\ \hline \\ I_{F}=600A \end{array}$	Tvj=25°C Tvj=125°C Tvj=125°C Tvj=150°C Tvj=150°C	- - - - - - - - - - - -	Rat 12 60 12 2.28 2.51 2.53 159.5 228.4 249.4 516.1 475.9 474.5 35.1 55.8 66.5	ting 00 00 00 - - - - - - - - - - - - - - -	Unit V A A V A ns

MPFF600R12MBF

R _{thJC}	Thermal resistance, junction to case	per diode	-	-	0.071	K/W
R _{thCH}	Thermalresistance, case to heatsink	per diode/ λ grease=1W/(m·K)	-	0.0395	-	K/W
T _{vjop}	Temperature under switching conditions		-40		150	°C

NTC Thermistor Characteristics

Symbol	Item	Conditions		Values	Unit	
Symbol	Item	Conditions	Min. Typ. M		Max.	
R ₂₅	Rated resistance	$T_{\rm C}=25^{\circ}{\rm C}$	-	5	-	kΩ
$\Delta R/R$	Deviation of resistance	$T_{C}=100^{\circ}C, R_{100}=493\Omega$	-5	-	5	%
P ₂₅	Power dissipation	$T_{\rm C}=25^{\circ}{\rm C}$	-	-	20	mW
B _{25/50}	B-constant	$R_2 = R_{25} exp[B_{25/50}(1/T_2 - 1/(298.15K))]$	-	3375	-	
B _{25/80}	B-constant	$R_2 = R_{25} exp[B_{25/80}(1/T_2-1/(298.15K))]$	-	3411	-	K
B _{25/100}	B-constant	$R_2 = R_{25} exp[B_{25/100}(1/T_2-1/(298.15K))]$	-	3433	-	

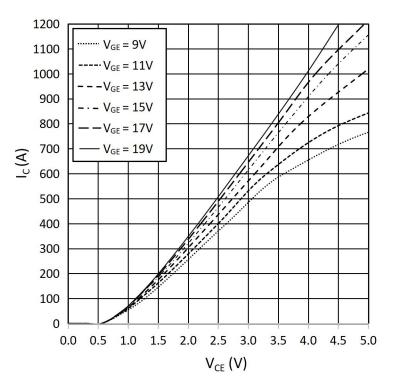
Module

Symbol	Item	Conditions	Rating		Unit	
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS,f=50Hz,t=1min	4000		V	
-	Material of module baseplate	-	Cu		-	
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al ₂ O ₃		-	
T _{stg}	Storage temperature	-	-40~125		5	°C
a 1 1	Item			Values		Unit
Symbol		Conditions	Min.	Тур.	Max.	
М	Mounting torque for module mounting	Screw M6	3.0	-	5.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
ds	Creepage distance	Terminal to terminal	-	13	-	
		Terminal to base plate	-	14.5	-	mm
1	Clearance	Terminal to terminal	-	10	-	
da		Terminal to base plate	-	12.5	-	mm
m	Weight	-	-	340	-	g

output characteristic IGBT, Inverter (typical)

 $I_{C} = f(V_{CE})$

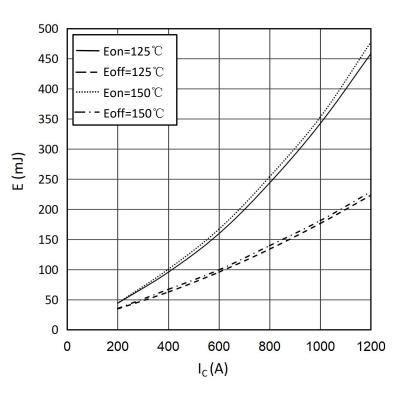
 $T_{vj}=150\,{}^\circ\!\mathrm{C}$





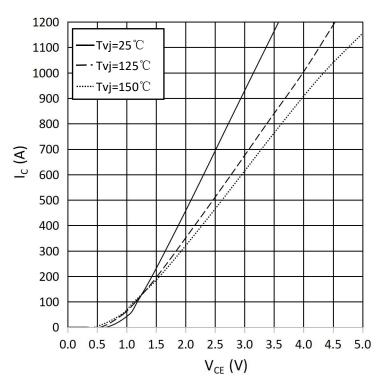
 $E_{on} = f(I_C), E_{off} = f(I_C)$

 $V_{GE} = \pm 15V, R_{Gon} = 5.1\Omega, R_{Goff} = 5.1\Omega, V_{CE} = 600V$



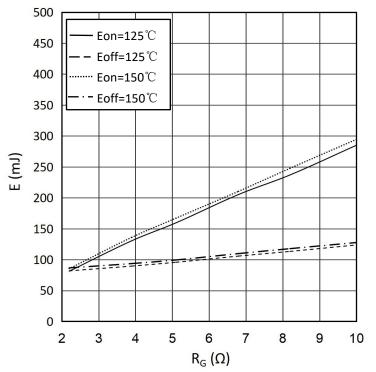
output characteristic IGBT, Inverter (typical)

 $I_{C} = f(V_{CE})$ $V_{GE} = 15 V$



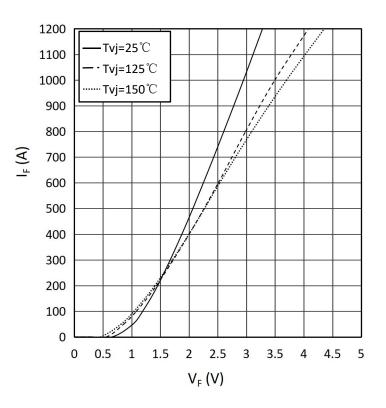
switching losses IGBT, Inverter(typical)

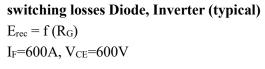
$$\begin{split} E_{\rm on} &= f\left(R_{\rm G}\right), \, E_{\rm off} = f\left(R_{\rm G}\right) \\ V_{\rm GE} &= \pm 15 \text{V}, \, I_{\rm C} = 600 \text{A}, \, V_{\rm CE} \text{=} \, 600 \text{V} \end{split}$$

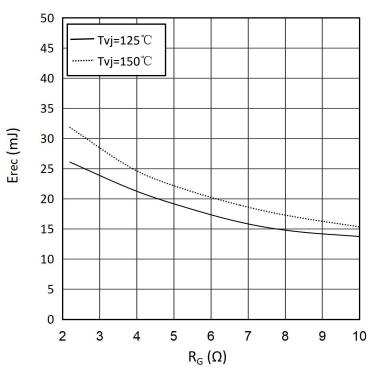


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forward characteristic of Diode, Inverter (typical) $I_F = f\left(V_F\right)$

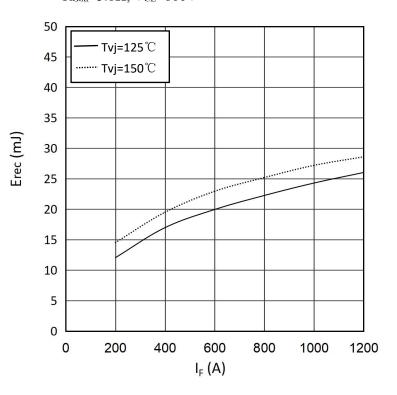




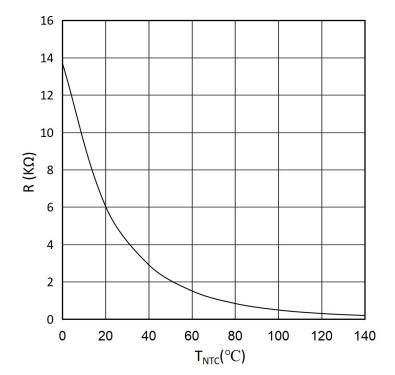


switching losses Diode, Inverter (typical)

$$\begin{split} E_{rec} &= f\left(I_{F}\right) \\ R_{Gon} &= 5.1 \Omega, \, V_{CE} &= 600 V \end{split}$$

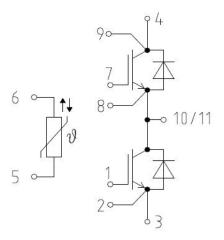


NTC-Thermistor-temperature characteristic(typical) R=f(T)

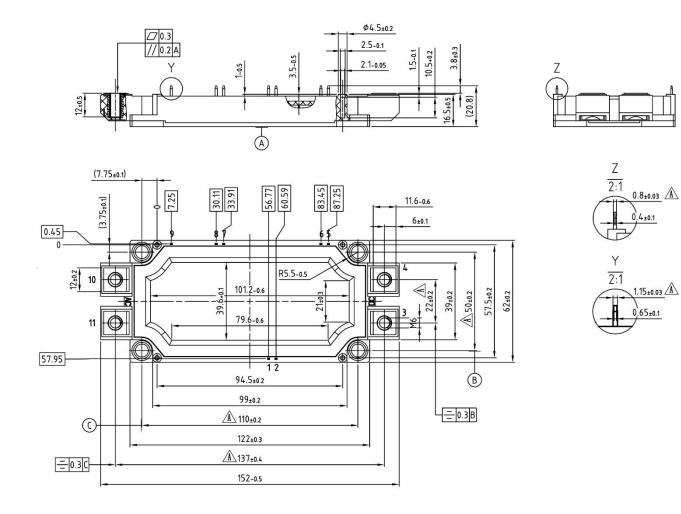


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Circuit diagram headline







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